

The 2N4339 JFET was selected because of its low IGSS age. Leakages of this level put the burden of circuit perform-(<100 pA), very-low ID(OFF) (<50 pA) and low pinchoff volt- ance on clean, solder-resin free, low leakage circuit layout.



Long Time Comparator

OV+ >10M 2N3684 OUTPUT **R1** 2N3686 INPUT O TL/H/6791-3

JFET AC Coupled Integrator

The 2N4393 is operated as a Miller integrator. The high Yfs of the 2N4393 (over 12,000 µmhos @ 5 mA) yields a stage gain of about 60. Since the equivalent capacitance looking into the gate is C times gain and the gate source resistance can be as high as 10 $M\Omega,$ time constants as long as a minute can be achieved.

This circuit utilizes the "µ-amp" technique to achieve very high voltage gain. Using C1 in the circuit as a Miller integrator, or capacitance multiplier, allows this simple circuit to handle very long time constants.



Ultra-High ZIN AC Unity Gain Amplifier

Nothing is left to chance in reducing input capacitance. The 2N4416, which has low capacitance in the first place, is operated as a source follower with bootstrapped gate bias

AN-32



The FET cascode video amplifier features very low input loading and reduction of feedback to almost zero. The 2N3823 is used because of its low capacitance and high $Y_{\rm fs}.$ Bandwidth of this amplifier is limited by ${\rm R}_{\rm L}$ and load capacitance.

resistor and drain. Any input capacitance you get with this circuit is due to poor layout techniques.



JFET Pierce Crystal Oscillator

The JFET Pierce crystal oscillator allows a wide frequency range of crystals to be used without circuit modification. Since the JFET gate does not load the crystal, good Q is maintained thus insuring good frequency stability.

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This FETVM replaces the function of the VTVM while at the same time ridding the instrument of the usual line cord. In addition, drift rates are far superior to vacuum tube circuits allowing a 0.5 volt full scale range which is impractical with most vacuum tubes. The low-leakage, low-noise 2N4340 is an ideal device for this application.





The 2N4416 JFET will provide noise figures of less than 3 dB and power gain of greater than 20 dB. The JFETs outstanding low crossmodulation and low intermodulation distortion provides an ideal characteristic for an input stage.

The output feeds into an LM171 used as a balanced mixer. This configuration greatly reduces L.O. radiation both into the antenna and into the I.F. strip and also reduces RF signal feedthrough.

AN-32



This preamplifier provides proper loading to a reluctance phono cartridge. It provides approximately 25 dB of gain at 1 kHz (2.2 mV input for 100 mV output), it features S + N/N ratio of better than -70 dB (referenced to 10 mV input at 1 kHz) and has a dynamic range of 84 dB (referenced to 1 kHz). The feedback provides for RIAA equalization.

AN-32



Variable Attenuator

The 2N3685 acts as a voltage variable resistor with an $R_{DS(ON)}$ of 800 Ω max. The 2N3685 JFET will have linear resistance over several decades of resistance providing an excellent electronic gain control.



TL/H/6791-13

Negative to Positive Supply Logic Level Shifter

This simple circuit provides for level shifting from any logic function (such as MOS) operating from minus to ground supply to any logic level (such as TTL) operating from a plus to ground supply. The 2N3970 provides a low $r_{ds(ON)}$ and fast switching times.



Voltage Controlled Variable Gain Amplifier

TL/H/6791-14

The 2N4391 provides a low $R_{DS(ON)}$ (less than 30 Ω). The tee attenuator provides for optimum dynamic linear range for attenuation and if complete turnoff is desired, attenua-

tion of greater than 100 dB can be obtained at 10 MHz providing proper RF construction techniques are employed.



Ultra-High Gain Audio Amplifier

Sometimes called the "JFET" μ amp," this circuit provides a very low power, high gain amplifying function. Since μ of a JFET increases as drain current decreases, the lower drain

current is, the more gain you get. You do sacrifice input dynamic range with increasing gain, however.



Level-Shifting-Isolation Amplifier

 $I_D = I_S.$

12/11/0/91-10

AN-32

The 2N4341 JFET is used as a level shifter between two op amps operated at different power supply voltages. The





JFET is ideally suited for this type of application because

The 2N3684 JFETs are used as Nixie tube drivers. Their V_p of 2-5 volts ideally matches DTL-TTL logic levels. Diodes are used to a +50 volt prebias line to prevent breakdown of the JFETs. Since the 2N3684 is in a TO-72 (4 lead TO-18) package, none of the circuit voltages appear on the can. The JFET is immune to almost all of the failure mechanisms found in bipolar transistors used for this application.

The 2N3069 JFET and 2N2219 bipolar have inherently high output impedance. Using R₁ as a current sensing resistor to provide feedback to the LM101 op amp provides a large amount of loop gain for negative feedback to enhance the true current sink nature of this circuit. For small current values, the 10k resistor and 2N2219 may be eliminated if the source of the JFET is connected to R₁.





Wein Bridge Sine Wave Oscillator

The logic voltage is applied simultaneously to the sample and hold JFETs. By matching input impedance and feedback resistance and capacitance, errors due to rds(ON) of the JFETs is minimized. The inherent matched rds(ON) and matched leakage currents of the FM1109 monolithic dual greatly improve circuit performance.



300K

LM101

106

1N914 LM103

1M

O Vour I = 10 Hz PEAK OUTPUT VOLTAGE

TL/H/6791-21

 $V_p = V_2 + 1V$

2.2 . . .



The 2N4416 features low input capacitance which makes this compound-series feedback buffer a wide-band unity gain amplifier.



This compound series-feedback circuit provides high input impedance and stable, wide-band gain for general purpose video amplifier applications.





This Colpitts-Crystal oscillator is ideal for low frequency crystal oscillator circuits. Excellent stability is assured because the 2N3823 JFET circuit loading does not vary with temperature.

Each stage provides 0° to 180° phase shift. By ganging the two stages, 0° to 360° phase shift is achieved. The 2N3070 JFETs are ideal since they do not load the phase shift networks.



DTL-TTL Controlled Buffered Analog Switch

This analog switch uses the 2N4860 JFET for its 25 ohm r_{ON} and low leakage. The LM102 serves as a voltage buffer. This circuit can be adapted to a dual trace oscilloscope

chopper. The DM7800 monolithic I.C. provides adequate switch drive controlled DTL-TTL logic levels.



 $\begin{array}{c} 20 \text{ MHz OSCILLATOR VALUES} \\ C1 &\simeq 700 \text{ pF} \quad L1 = 1.3 \ \mu\text{H} \\ C2 &= 75 \text{ pF} \quad L2 = 107 \ \%^* \ \text{DIA} \ \%^* \ \text{LONG} \\ V_{DD} &= 16V \qquad I_D = 1 \ \text{mA} \\ 20 \ \text{MHz OSCILLATOR PERFORMANCE} \\ LOW DISTORTION 20 \ \text{MHz OSC.} \\ 2ND \ \text{HARMONIC} \ -60 \ \text{dB} \end{array}$

3RD HARMONIC > -70 dB

TL/H/6791-28

Low Distortion Oscillator

The 2N4416 JFET is capable of oscillating in a circuit where harmonic distortion is very low. The JFET local oscillator is excellent when a low harmonic content is required for a good mixer circuit.







 R_1 senses current flow of a power supply. The JFET is used as a buffer because $I_D = I_S$, therefore the output monitor voltage accurately reflects the power supply current flow.



Low Cost High Level Preamp and Tone Control Circuit

This preamp and tone control uses the JFET to its best advantage; as a low noise high input impedance device. All device parameters are non-critical yet the circuit achieves harmonic distortion levels of less than 0.05% with a S/N

ratio of over 85 dB. The tone controls allow 18 dB of cut and boost; the amplifier has a 1 volt output for 100 mV input at maximum level.

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The 2N3069 JFET and 2N2219 bipolar serve as voltage devices between the output and the current sensing resistor, R_1 . The LM101 provides a large amount of loop gain to assure that the circuit acts as a current source. For small values of current, the 2N2219 and 10k resistor may be eliminated with the output appearing at the source of the 2N3069.

Schmitt Trigger

This Schmitt trigger circuit is "emitter coupled" and provides a simple comparator action. The 2N3069 JFET places very little loading on the measured input. The 2N3565 bipolar is a high h_{FE} transistor so the circuit has fast transition action and a distinct hysteresis loop.

